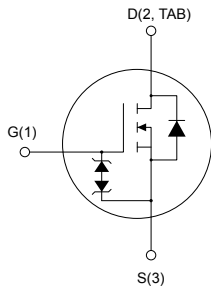
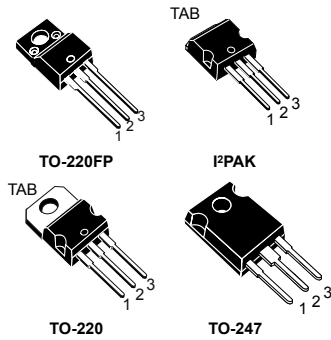




# STF33N60M2, STI33N60M2 STP33N60M2, STW33N60M2

Datasheet

N-channel 600 V, 108 mΩ typ., 26 A MDmesh M2 Power MOSFET  
in a TO-220FP, I<sup>2</sup>PAK, TO-220 and TO-247 packages



AM01476v1\_tab

## Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STF33N60M2	600 V	125 mΩ	26 A
STI33N60M2			
STP33N60M2			
STW33N60M2			

- Extremely low gate charge
- Excellent output capacitance (C<sub>oss</sub>) profile
- 100% avalanche tested
- Zener-protected

## Applications

- Switching applications
- LLC resonant, converters

## Description

These devices are N-channel Power MOSFETs developed using the MDmesh M2 technology. Thanks to their strip layout and improved vertical structure, these devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high-efficiency converters.



### Product status links

[STF33N60M2](#)

[STI33N60M2](#)

[STP33N60M2](#)

[STW33N60M2](#)

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-220FP	I <sup>2</sup> PAK, TO-220, TO-247	
V <sub>DS</sub>	Drain-source voltage	600		V
V <sub>GS</sub>	Gate-source voltage	±25		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	26 <sup>(1)</sup>	26	A
	Drain current (continuous) at T <sub>C</sub> = 100 °C	16 <sup>(1)</sup>	16	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	104 <sup>(1)</sup>	104	A
P <sub>TOT</sub>	Total power dissipation at T <sub>C</sub> = 25 °C	35	190	W
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	15		V/ns
dv/dt <sup>(4)</sup>	MOSFET dv/dt ruggedness	50		V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T <sub>C</sub> = 25 °C)	2.5		kV
T <sub>stg</sub>	Storage temperature range	-50 to 150		°C
T <sub>J</sub>	Operating junction temperature range			

- Limited by maximum junction temperature.
- Pulse width is limited by safe operating area.
- $I_{SD} \leq 26 \text{ A}$ ,  $di/dt \leq 400 \text{ A}/\mu\text{s}$ ,  $V_{DS} (\text{peak}) < V_{(BR)DSS}$ ,  $V_{DD} = 400 \text{ V}$
- $V_{DD} \leq 480 \text{ V}$

**Table 2. Thermal data**

Symbol	Parameter	Value			Unit
		TO-220FP	I <sup>2</sup> PAK TO-220	TO-247	
R <sub>thJC</sub>	Thermal resistance, junction-to-case	3.6	0.66		°C/W
R <sub>thJA</sub>	Thermal resistance, junction-to-ambient	62.5		50	°C/W

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
I <sub>AR</sub>	Avalanche current, repetitive or not repetitive (pulse width limited by T <sub>J</sub> max.)	5	A
E <sub>AS</sub>	Single pulse avalanche energy (starting T <sub>J</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	450	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified).

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0\text{ V}$	600			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$ , $T_C = 125\text{ °C}^{(1)}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 13\text{ A}$		108	125	$\text{m}\Omega$

1. Specified by design, not tested in production.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	1781	-	$\text{pF}$
$C_{oss}$	Output capacitance		-	85	-	$\text{pF}$
$C_{riss}$	Reverse transfer capacitance		-	2.5	-	$\text{pF}$
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}$ , $V_{GS} = 0\text{ V}$	-	135	-	$\text{pF}$
$R_g$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_D = 0\text{ V}$	-	5.2	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 26\text{ A}$ , $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 19. Test circuit for gate charge behavior)	-	45.5	-	$\text{nC}$
$Q_{gs}$	Gate-source charge		-	9.9	-	$\text{nC}$
$Q_{gd}$	Gate-drain charge		-	18.5	-	$\text{nC}$

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

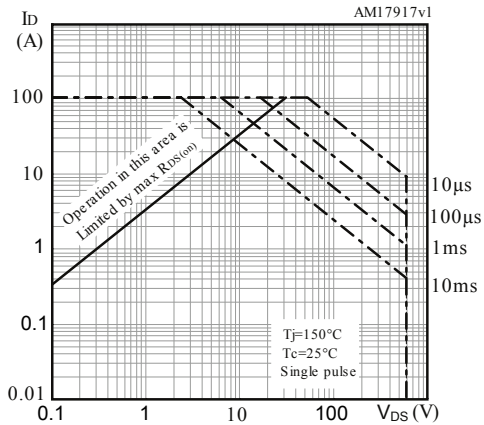
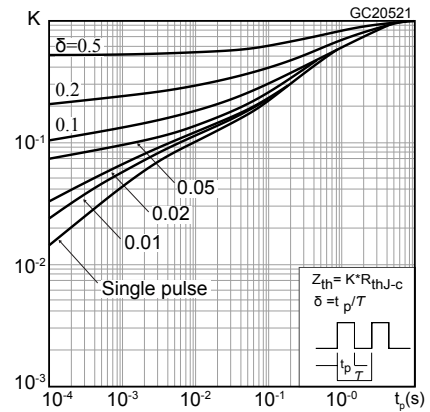
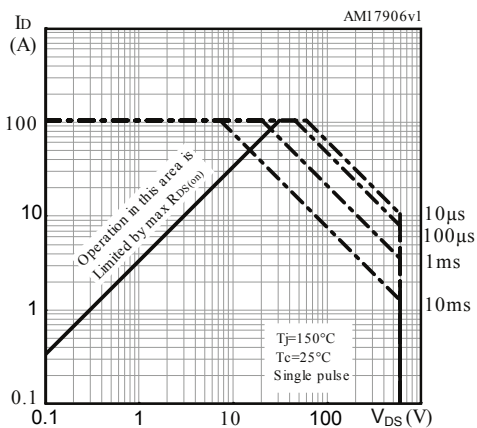
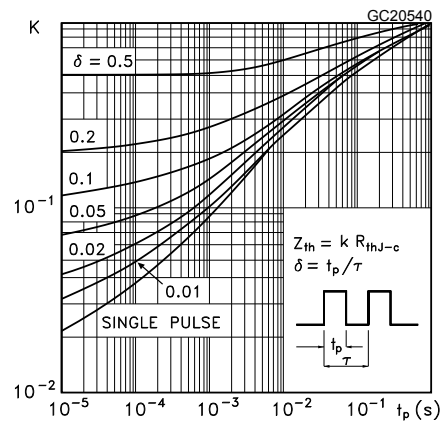
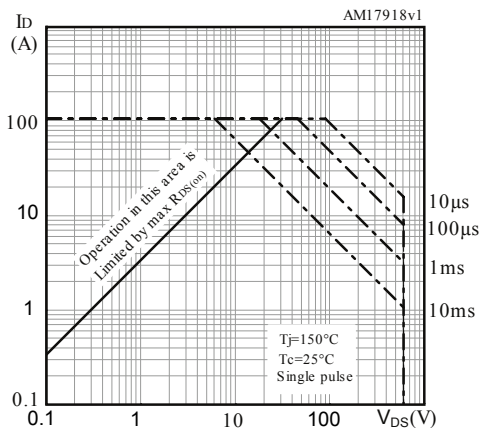
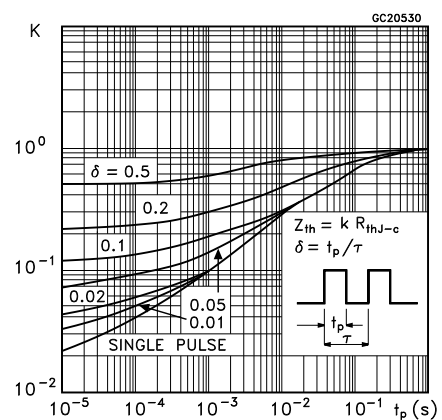
**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 13\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$	-	16	-	ns
$t_r$	Rise time		-	9.6	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 18. Test circuit for resistive load switching times and Figure 23. Switching time waveform)	-	109	-	ns
$t_f$	Fall time		-	9	-	ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		26	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		104	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 26\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 26\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	-	375		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$	-	5.6		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see Figure 20. Test circuit for inductive load switching and diode recovery times)	-	30		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 26\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	-	478		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$	-	7.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see Figure 20. Test circuit for inductive load switching and diode recovery times)	-	35.5		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

**2.1 Electrical characteristics (curves)**
**Figure 1. Safe operating area for TO-220FP**

**Figure 2. Thermal impedance for TO-220FP**

**Figure 3. Safe operating area for I<sup>2</sup>PAK and TO-220**

**Figure 4. Thermal impedance for I<sup>2</sup>PAK and TO-220**

**Figure 5. Safe operating area for TO-247**

**Figure 6. Thermal impedance for TO-247**


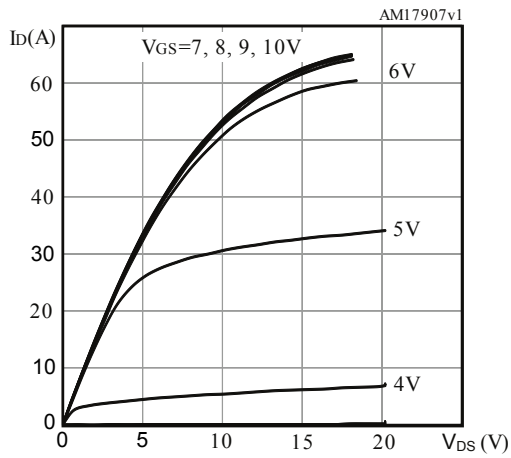
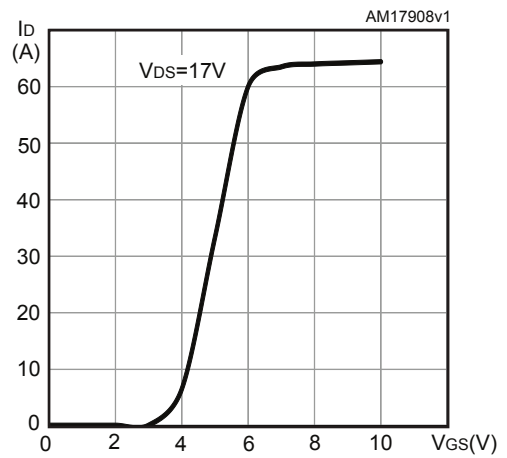
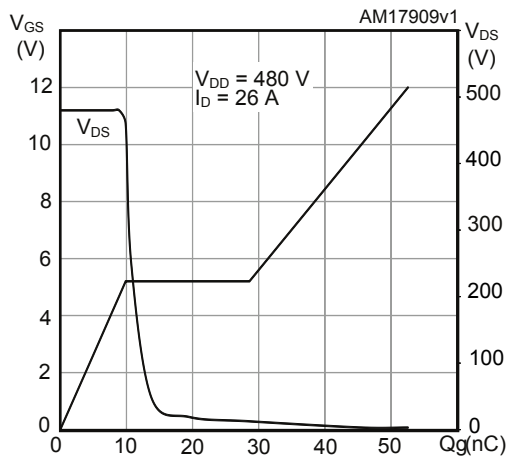
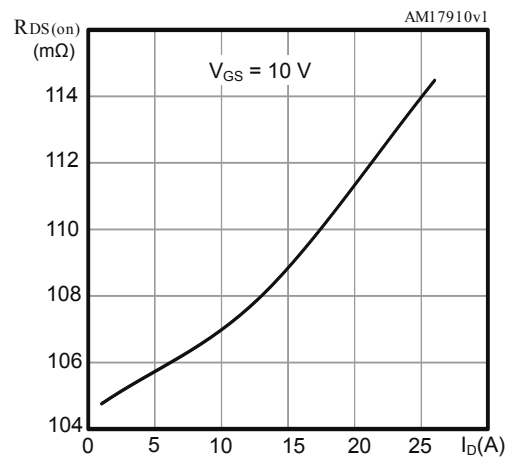
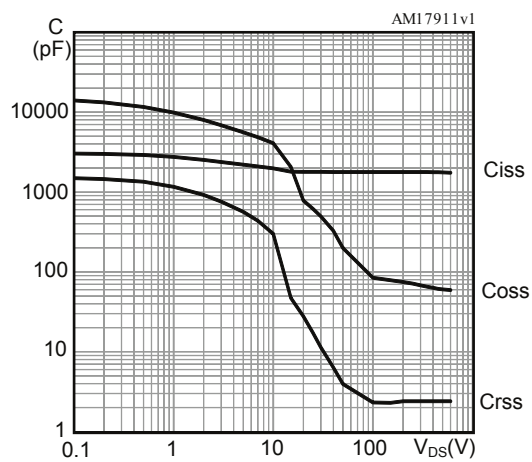
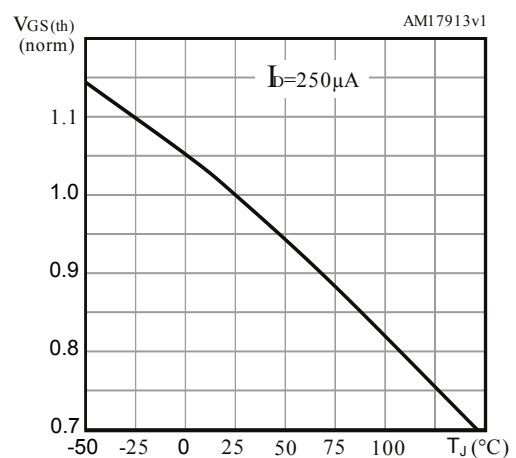
**Figure 7. Output characteristics**

**Figure 8. Transfer characteristics**

**Figure 9. Gate charge vs gate-source voltage**

**Figure 10. Static drain-source on-resistance**

**Figure 11. Capacitance variations**

**Figure 12. Normalized gate threshold voltage vs temperature**


Figure 13. Normalized on-resistance vs temperature

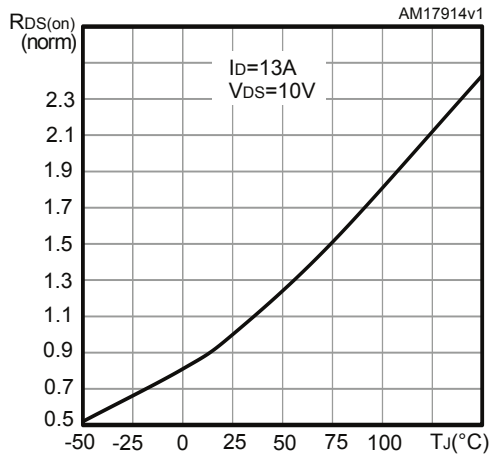


Figure 14. Source-drain diode forward characteristics

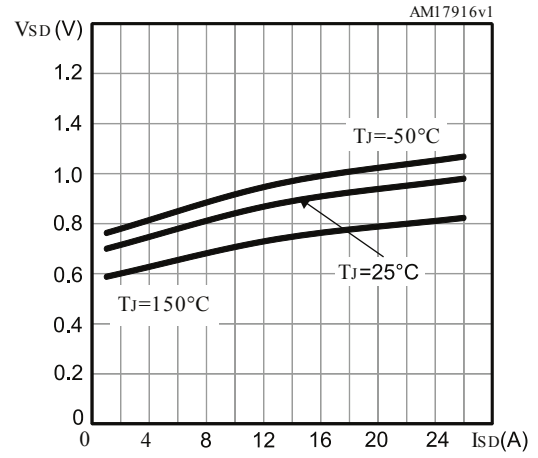


Figure 15. Normalized V<sub>(BR)DSS</sub> vs temperature

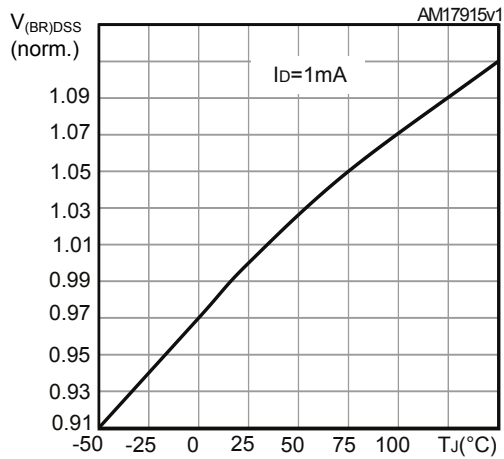


Figure 16. Output capacitance stored energy

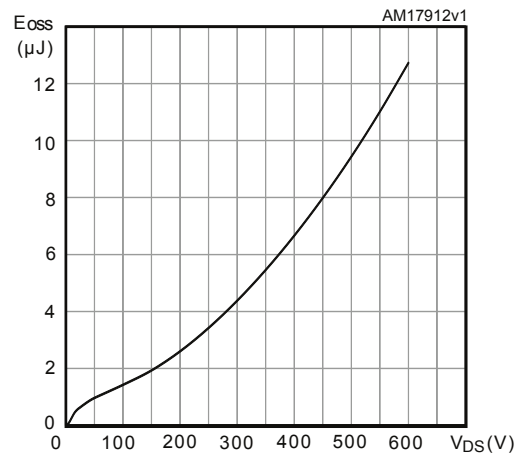
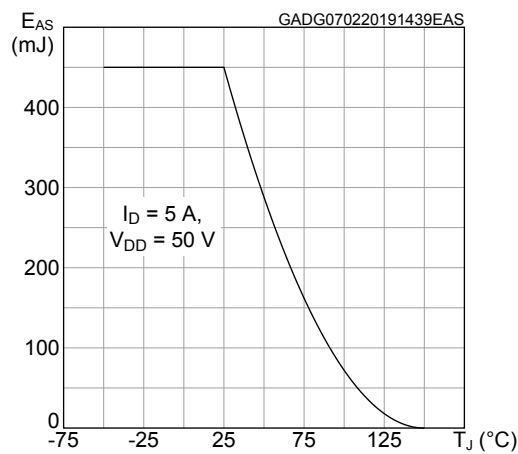
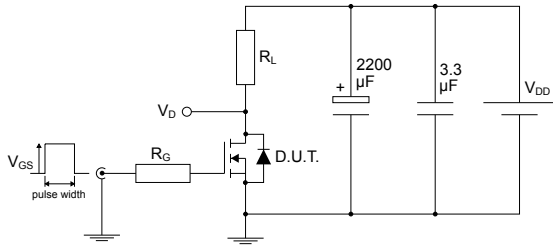


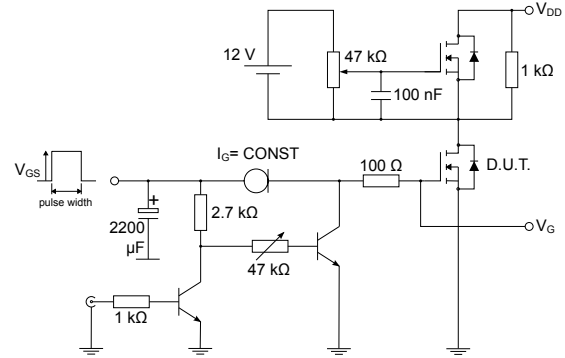
Figure 17. Maximum avalanche energy vs temperature



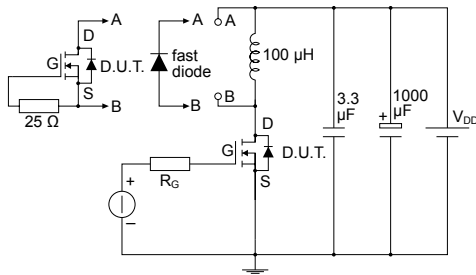
### 3 Test circuits

**Figure 18. Test circuit for resistive load switching times**


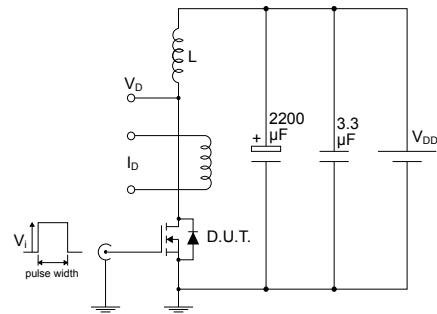
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**Figure 19. Test circuit for gate charge behavior**


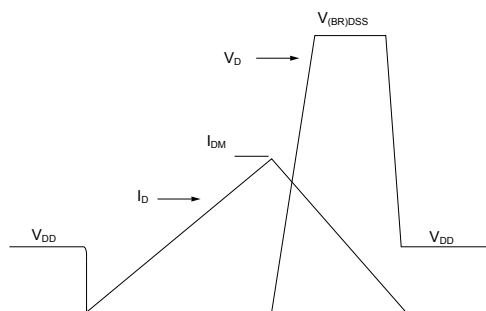
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**Figure 20. Test circuit for inductive load switching and diode recovery times**


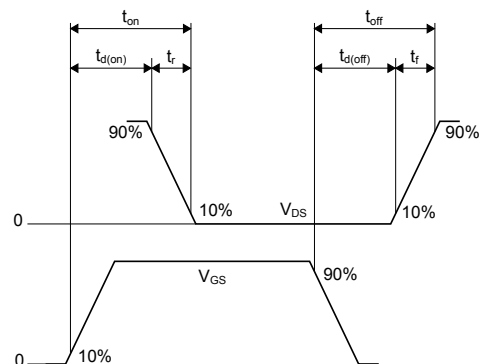
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**Figure 21. Unclamped inductive load test circuit**


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**Figure 22. Unclamped inductive waveform**


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**Figure 23. Switching time waveform**


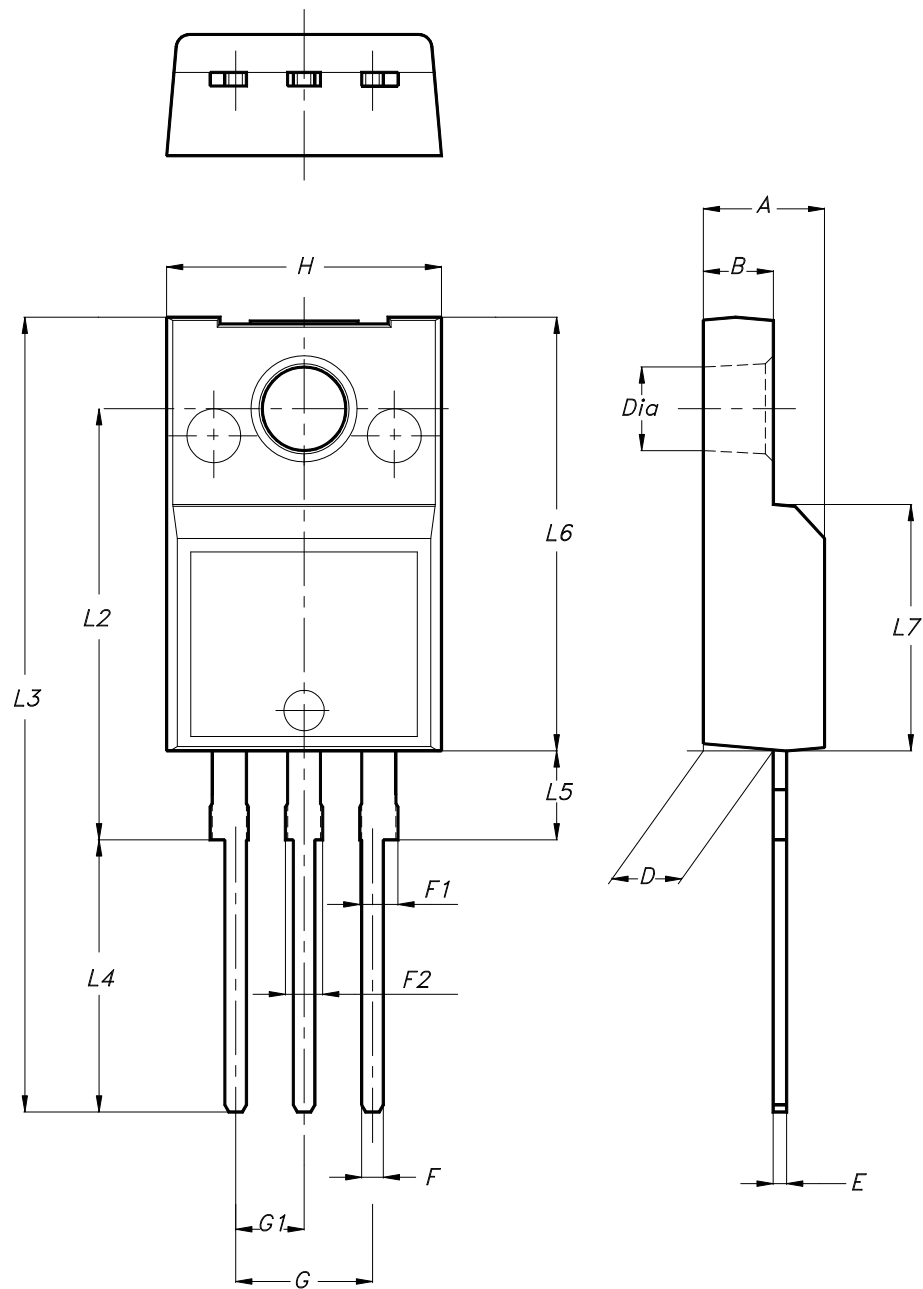
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## 4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 TO-220FP type B package information

Figure 24. TO-220FP type B package outline



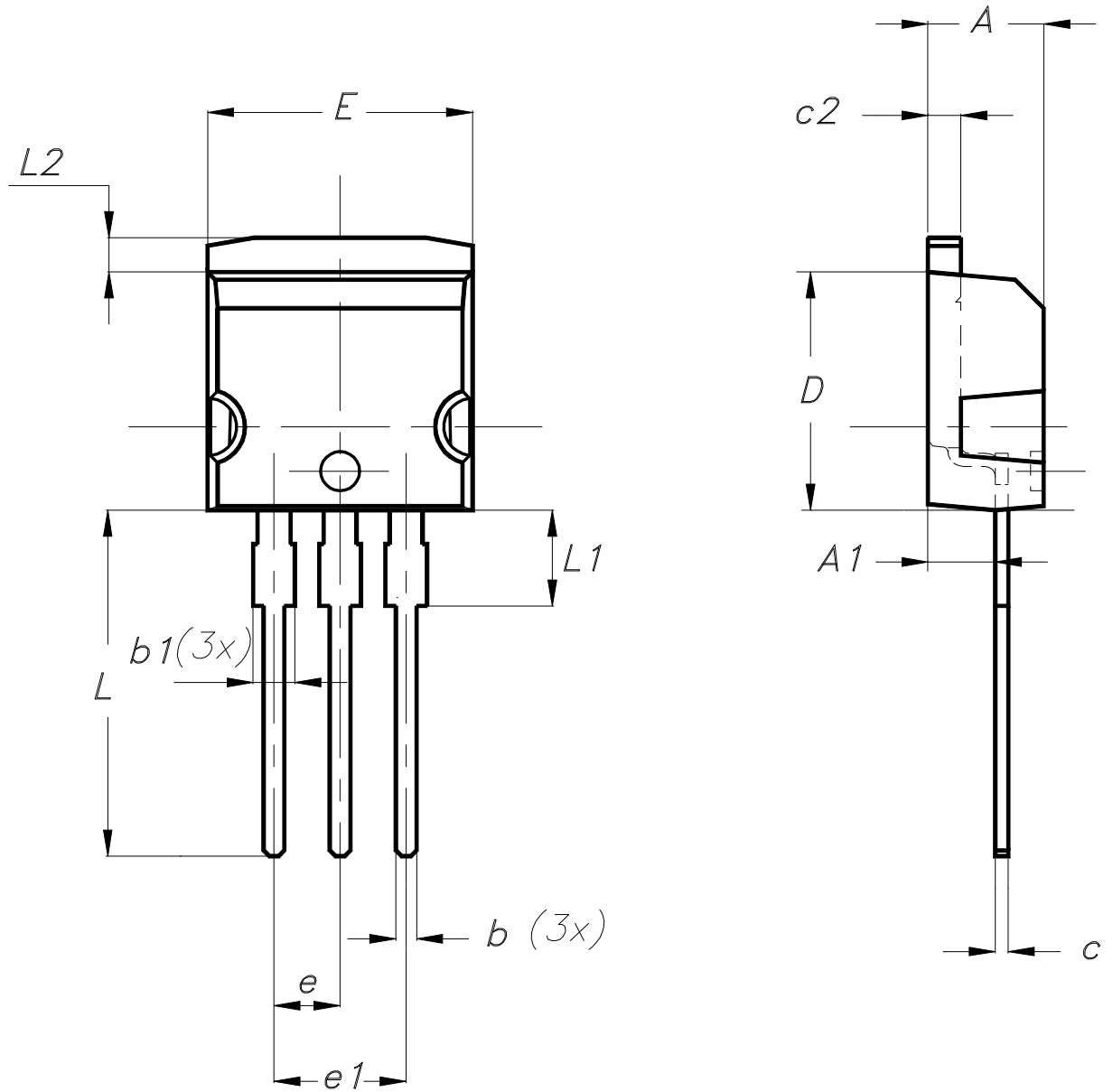
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**Table 8. TO-220FP type B package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

4.2 I<sup>2</sup>PAK package information

Figure 25. I<sup>2</sup>PAK package outline



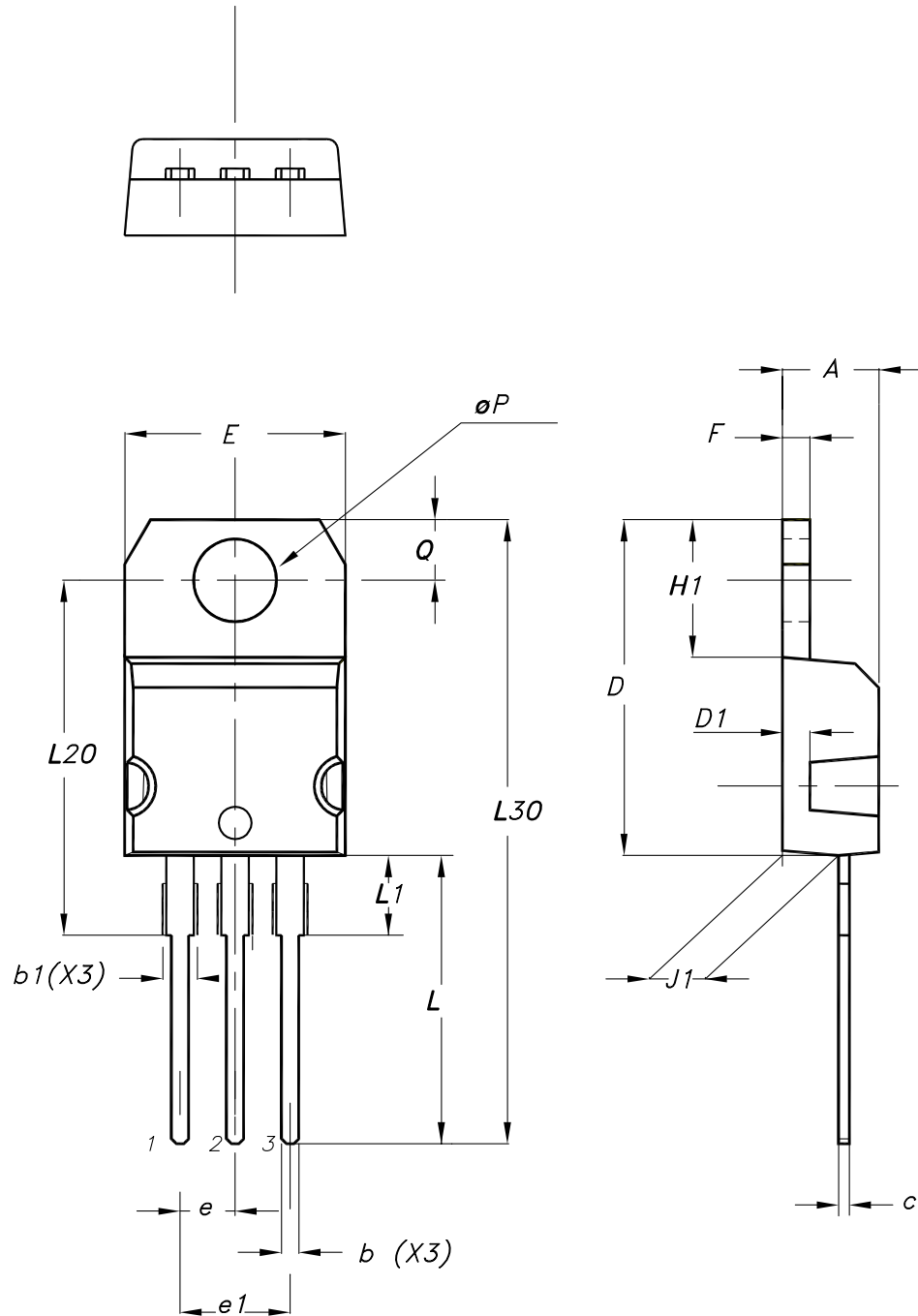
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**Table 9. I<sup>2</sup>PAK package mechanical data**

Dim.	mm	
	Min.	Max.
A	4.40	4.60
A1	2.40	2.72
b	0.61	0.88
b1	1.14	1.70
c	0.49	0.70
c2	1.23	1.32
D	8.95	9.35
e	2.40	2.70
e1	4.95	5.15
E	10.00	10.40
L	13.00	14.00
L1	3.50	3.93
L2	1.27	1.40

### 4.3 TO-220 type A package information

Figure 26. TO-220 type A package outline



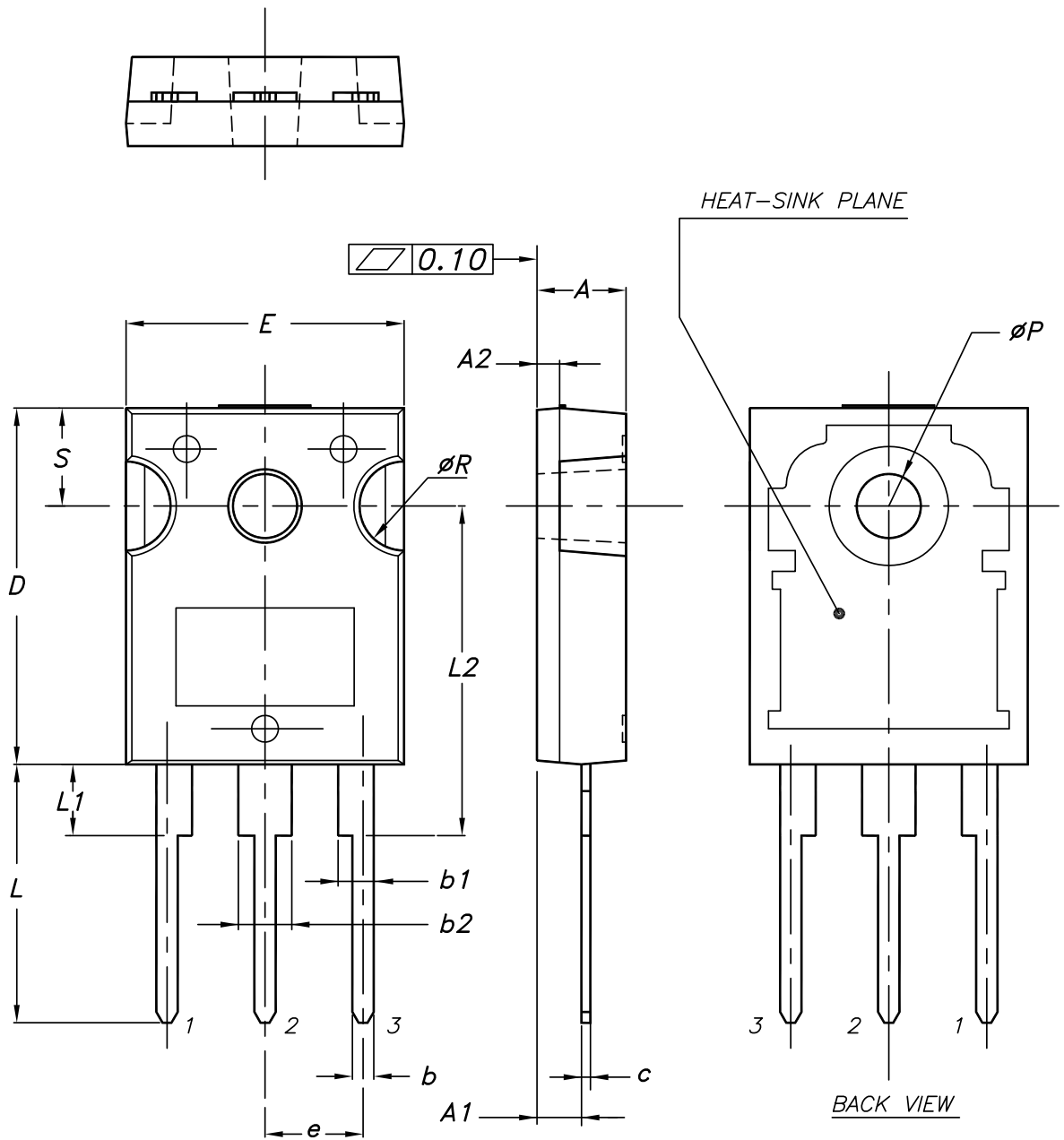
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**Table 10. TO-220 type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

#### 4.4 TO-247 package information

Figure 27. TO-247 package outline



0075325\_11

**Table 11. TO-247 package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
A2		1.27	
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70



## 5 Ordering information

Table 12. Order codes

Order code	Marking	Package	Packing
STF33N60M2	33N60M2	TO-220FP	Tube
STI33N60M2		I <sup>2</sup> PAK	
STP33N60M2		TO-220	
STW33N60M2		TO-247	

## Revision history

**Table 13. Document revision history**

Date	Version	Changes
13-Sep-2013	1	First release.
19-Nov-2013	2	Modified: $R_{DS(on)}$ and $I_D$ values in cover page Modified: values in <i>Table 4</i> Modified: $R_{DS(on)}$ typical and maximum values in <i>Table 5</i> , the entire typical values in <i>Table 6, 7 and 8</i> Added: <i>Section 2.1: Electrical characteristics (curves)</i> Minor text changes
14-Jun-2019	3	Removed maturity status indication from cover page. Updated title, <i>features</i> and <i>description</i> . Updated <i>Table 3. Avalanche characteristics</i> . Added <i>Figure 17. Maximum avalanche energy vs temperature</i> . Minor text changes
12-Feb-2026	4	Updated <a href="#">Section 4: Package information</a> . Minor text changes.



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